



REMARKS

Reconsideration and allowance of the above-referenced application are respectfully requested.

Initially, the indication that claims 1-3, 6-8, 32-34, and 38 are allowed is appreciatively noted.

The remaining claims 11-13, 15, 21-23, 25-27, 29, and 31 stand rejected under 35 U.S.C. 102(b) as allegedly being anticipated by the Japanese document JP 3-82164. The claims 11, 16, 21, and 25 have been amended to recite a gate electrode formed of a first metal layer and a second metal layer on the first metal layer. These comprise different materials from one another, and are provided to distinguish over the Japanese prior art 3-82164.

Claims 21-23, and 37 stand rejected under 35 U.S.C. 102(b) as allegedly being anticipated by Lee. These contentions are also obviated by the amendment of the claims herein.

Claim 25 stands rejected under judicially created obviousness-type double patenting as being unpatentable over claim 15 of the '378 patent. Since claim 25 is amended herein, this obviates the rejection.

We have requested the drawings be corrected to include reference numerals as required.

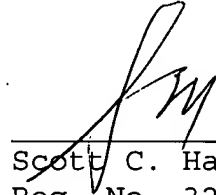
In view of the above amendments and remarks, therefore, all of the claims should be in condition for allowance. A formal notice to that effect is respectfully solicited.

Please apply any charges or credits to Deposit Account No. 06-1050.

Respectfully submitted,

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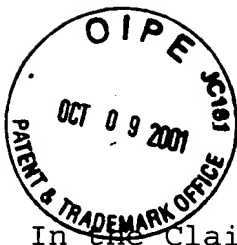


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VERSION TO SHOW CHANGES MADE

In the Claims:

Claims 11, 15, 16, 20, 21, and 25 have been amended as follows.

11. (Amended) A semiconductor device comprising:

a semiconductor layer;

a gate insulating film formed on said semiconductor layer;

a first conductive layer formed on said gate insulating film [wherein said first conductive layer extends over said channel region];

a second conductive layer electrically connected to said first conductive layer; and

an insulating film comprising oxide of said first and second conductive layers,

wherein [each of said first and second conductive layers] said first conductive layer comprises a first material selected from the group consisting of molybdenum, tantalum, aluminum, chromium, nickel, zirconium, titanium, palladium, silver, copper, and cobalt,

wherein said second conductive layer comprises a second material which is different from said first material,

wherein a width of said first conductive layer is narrower than that of said second conductive layer, and

wherein said insulating film is formed on at least side surfaces of said first and second conductive layers.

15. (Amended) A semiconductor device according to claim 11, [further comprising] wherein said semiconductor layer comprises a pair of impurity regions in said semiconductor layer with [said] a channel region interposed therebetween.

16. (Amended) A semiconductor device comprising:

a semiconductor layer;

a gate insulating film formed on said semiconductor layer;

a first conductive layer formed on said gate insulating film [wherein said first conductive layer extends over said channel region];

a second conductive layer electrically connected to said first conductive layer wherein said first conductive layer comprises a different material from said second conductive layer; and

an insulating film comprising oxide of said first and second conductive layers,

wherein [each of said first and second conductive layers] said first conductive layer comprises a first material selected from the group consisting of molybdenum, tantalum, aluminum, chromium, nickel, zirconium, titanium, palladium, silver, copper, and cobalt,

wherein said second conductive layer comprises a second material which is different from said first material,

wherein a width of said first conductive layer is narrower than that of said second conductive layer, and

wherein said insulating film is formed on side surfaces of said first and second conductive layers and a top surface of said second conductive layer.

20. (Amended) A semiconductor device according to claim 11, [further comprising] wherein said semiconductor layer comprises a pair of impurity regions in said semiconductor layer with [said] a channel region interposed therebetween.

21. (Amended) A semiconductor device comprising:

a gate electrode comprising a first conductive layer formed on an insulating surface and a second conductive layer formed on said first conductive layer;

an insulating film formed on said gate electrode;

a semiconductor layer comprising a source region, a drain region, and a channel region formed on said insulating film,

wherein said first conductive layer [and said second layer] comprises a first material selected from the group consisting of molybdenum, tantalum, aluminum, chromium, nickel, zirconium, titanium, palladium, silver, copper, and cobalt,

wherein said second conductive layer comprises a second material which is different from said first material, and

wherein a width of said second conductive layer is narrower than that of said first conductive layer.

25. (Amended) A semiconductor device comprising:

a gate electrode comprising a first conductive layer formed on an insulating surface and a second conductive layer formed on said first conductive layer;

a gate insulating film formed on said gate electrode;

a semiconductor layer comprising a source region, a drain region, and a channel region formed on said insulating film, and

an insulating film comprising oxide of said first and second conductive layers,

wherein said first conductive layer [and said second layer] comprises a first material selected from the group consisting of molybdenum, tantalum, aluminum, chromium, nickel, zirconium, titanium, palladium, silver, copper, and cobalt,

wherein said second conductive layer comprises a second material which is different from said first material, and

wherein a width of said second conductive layer is narrower than that of said first conductive layer, and

wherein said insulating film is formed on at least side surfaces of said first and second conductive layers.